

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	435	257/10 and (emit\$5)	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 14:30
L2	14	("4772489"   "5242538"   "5385862"   "5805624"   "5904860"   "5948161"   "5985747"   "6008502"   "6045978"   "6046088"   "6080529"   "6096592"   "6171917"   "6265287").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 13:31
L3	5	("5691608").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/04/21 13:31
L4	13	("3449620"   "3579015"   "3720859"   "3845243"   "3863023"   "4067047"   "4259678"   "4303930"   "4325084"   "4361781"   "4368467"   "4701811").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 13:34
L5	0	("5691608").URPN.	USPAT	OR	ON	2005/04/21 13:34
L6	25	microdischarge and (cavity) and (semiconductor or (n-type) or (p-type))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 14:35
L7	2	("3793552"   "6695664").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 14:33
L8	56420	(cavity) and (semiconductor or (n-type) or (p-type))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 14:35
L9	2897	(cavity with (taper\$3 or narrow\$4)) and (semiconductor or (n-type) or (p-type))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 14:35
L10	948	(cavity with (taper\$3 or narrow\$4)) and (semiconductor or (n-type) or (p-type)) and (electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 14:36
L11	716	(cavity with (taper\$3 or narrow\$4)) and (semiconductor or (n-type) or (p-type)) and (electron) and (insulat\$4 or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 15:16

L12	2	("6147349").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/04/21 15:16
S1	0	(method and (manufactur\$4 or fabricat\$4) and dishcharge).ti. and cavity and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 08:20
S2	4154	(method and (manufactur\$4 or fabricat\$4)).ti. and cavity and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/15 13:32
S3	3	(method and (manufactur\$4 or fabricat\$4) and discharge).ti. and cavity and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/15 13:33
S4	45	(method and (manufactur\$4 or fabricat\$4) and discharge).ti. and cavity	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/15 13:37
S5	328	(method and (manufactur\$4 or fabricat\$4) and discharge).ti. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/15 13:37
S6	12	"445"/\$ and (method and (manufactur\$4 or fabricat\$4) and discharge).ti. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/15 13:39
S7	117	(cavity with etch\$4 with (n-type or p-type)) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 14:31
S8	4	(cavity with etch\$4 with (n-type or p-type)) and semiconductor and lamp	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/15 13:40
S9	2	("6016027").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/09/15 13:57
S10	19	313/356 and (semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 08:27
S11	2	("6016027").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/11/19 08:21

S12	2	("5686789").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/11/19 08:21
S13	2	("6139384").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/11/19 08:22
S14	2	("6082294").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/11/19 08:22
S15	2	("5939829").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/11/19 08:22
S16	934	313/356	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 08:27
S17	25	313/356 and (semiconductor or silicone or Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 10:50
S18	39	313/356 and (semiconductor or silicone or Si or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 08:40
S19	2	("5387805").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/11/19 08:33
S20	14	("4110775"   "4672624"   "5013902"   "5055979"   "5062116"   "5200973"   "5387805"   "5686789"   "5939829"   "6016027"   "6082294"   "6139384"   "6353289"   "6563257").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/11/19 08:34
S21	39	313/356 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 08:42
S22	40	313/618 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 08:46
S23	199	313/631 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 09:14

S24	95	313/632 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 09:19
S25	578	313/498 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 10:45
S26	67	313/567 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 10:50
S27	73	313/574 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 10:56
S28	437	257/12 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 11:38
S29	423	257/656 and (semiconductor or silicone or Si or silicon or p-type or n-type)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/11/19 13:38
S30	18	"6016027"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/07 10:31
S31	5	"5691608"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/07 10:34
S32	1	"313"/\$ and (restricted near getter).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/07 10:35
S33	6	("5686789"   "5939829"   "6082294"   "6139384"   "6194833"   "6346770").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 10:43
S34	14	("4110775"   "4672624"   "5013902"   "5055979"   "5062116"   "5200973"   "5387805"   "5686789"   "5939829"   "6016027"   "6082294"   "6139384"   "6353289"   "6563257").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 10:43
S35	5	("5686789"   "5939829"   "6016027"   "6082294"   "6139384").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 10:48

S36	5	("5185552"   "5327475"   "5499282"   "6016027"   "6031241").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 10:49
S37	19	("3487254"   "3697797"   "3908147"   "3970887"   "4060748"   "4459636"   "4698546"   "4808883"   "4890031"   "4988918"   "5438343"   "5496199"   "5514847"   "5926496"   "5990620"   "6016027"   "6139384"   "6194833").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 10:49
S38	15	("3487254"   "3697797"   "3908147"   "3970887"   "4060748"   "4698546"   "4808883"   "4890031"   "4988918"   "5438343"   "5496199"   "5514847"   "5926496"   "5990620").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 10:52
S39	12	("3487254"   "3697797"   "3908147"   "3970887"   "4060748"   "4808883"   "4890031"   "4988918"   "5438343"   "5496199"   "5514847").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/07 10:53
S40	160	372/87 and (semiconductor or silicone or Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 10:46
S41	26	313/356 and (semiconductor or silicone or Si or (n-type) or (p-type))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 10:51
S42	27	313/618 and (semiconductor or silicone or Si or (n-type) or (p-type))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 10:51
S43	161	372/87 and (semiconductor or silicone or Si or (n-type) or (p-type))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 10:54
S44	379	438/20 and (semiconductor or silicone or Si or (n-type) or (p-type))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/04/21 10:54
S45	2	("5387805").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/04/21 10:54

S46	2	("4502070"   "5202750").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 10:55
S47	2	("4717940"   "5034785").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 10:55
S48	30	("5202750").URPN.	USPAT	OR	ON	2005/04/21 10:56
S49	26	("4048649"   "4329705"   "4725562"   "4799095"   "4945394"   "4981551"   "5014102"   "5087576"   "5168331"   "5170231"   "5202750"   "5233215"   "5264713"   "5270554"   "5304821"   "5323040"   "5331194"   "5396085"   "5459107"   "5488236"   "5489787"   "5506421"   "5539217"   "5679966"   "5719409"   "5723891").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 13:19